

NGTB40N120L3WG

IGBT - Ultra Field Stop

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Ultra Field Stop Trench construction, and provides superior performance in demanding switching applications, offering both low on-state voltage and minimal switching loss. The IGBT is well suited for motor driver applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for Low V_{CEsat}
- These are Pb-Free Devices

Typical Applications

- Solar Inverter and UPS
- Industrial Switching
- Welding

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	1200	V
Collector current @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$	I_C	160 40	A
Pulsed collector current, T_{pulse} limited by T_{Jmax}	I_{CM}	160	A
Diode forward current @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$	I_F	160 40	A
Diode pulsed current, T_{pulse} limited by T_{Jmax}	I_{FM}	160	A
Gate-emitter voltage Transient gate-emitter voltage ($t_{pulse} = 5 \mu s, D < 0.10$)	V_{GE}	± 20 ± 30	V
Power Dissipation @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$	P_D	454 227	W
Operating junction temperature range	T_J	-55 to +175	$^{\circ}C$
Storage temperature range	T_{stg}	-55 to +175	$^{\circ}C$
Lead temperature for soldering, 1/8" from case for 5 seconds	T_{SLD}	260	$^{\circ}C$

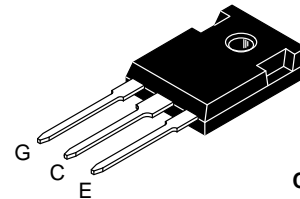
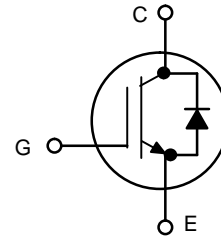
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



ON Semiconductor[®]

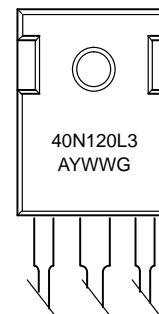
www.onsemi.com

40 A, 1200 V
 $V_{CEsat} = 1.55 V$
 $E_{off} = 1.5 mJ$



**TO-247
CASE 340AL**

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTB40N120L3WG	TO-247 (Pb-Free)	30 Units / Rail

NGTB40N120L3WG

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT	$R_{\theta JC}$	0.33	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction-to-case, for Diode	$R_{\theta JC}$	0.61	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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STATIC CHARACTERISTIC

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$	$V_{(BR)CES}$	1200	–	–	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 175^{\circ}\text{C}$	V_{CEsat}	–	1.55 2.0	1.8 –	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 400\ \mu\text{A}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 175^{\circ}\text{C}$	I_{CES}	–	– 0.5	0.4	mA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	–	–	200	nA

Input capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{ies}	–	4912	–	pF
Output capacitance		C_{oes}	–	140	–	
Reverse transfer capacitance		C_{res}	–	80	–	
Gate charge total	$V_{CE} = 600\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	Q_g	–	220	–	nC
Gate to emitter charge		Q_{ge}	–	42	–	
Gate to collector charge		Q_{gc}	–	110	–	

SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-on delay time	$T_J = 25^{\circ}\text{C}$ $V_{CC} = 600\text{ V}, I_C = 40\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 15\text{ V}$	$t_{d(on)}$	–	18	–	ns	
Rise time		t_r	–	30	–		
Turn-off delay time		$t_{d(off)}$	–	150	–		
Fall time			t_f	–	131	–	mJ
Turn-on switching loss		E_{on}	–	1.5	–		
Turn-off switching loss		E_{off}	–	1.5	–		
Total switching loss		E_{ts}	–	3.0	–		
Turn-on delay time	$T_J = 175^{\circ}\text{C}$ $V_{CC} = 600\text{ V}, I_C = 40\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 15\text{ V}$	$t_{d(on)}$	–	18	–	ns	
Rise time		t_r	–	31	–		
Turn-off delay time		$t_{d(off)}$	–	156	–		
Fall time			t_f	–	220	–	mJ
Turn-on switching loss		E_{on}	–	2.0	–		
Turn-off switching loss		E_{off}	–	2.3	–		
Total switching loss		E_{ts}	–	4.3	–		

DIODE CHARACTERISTICS

Forward voltage	$V_{GE} = 0\text{ V}, I_F = 40\text{ A}$ $V_{GE} = 0\text{ V}, I_F = 40\text{ A}, T_J = 175^{\circ}\text{C}$	V_F	–	3.0 2.8	3.4 –	V
Reverse recovery time	$T_J = 25^{\circ}\text{C}$ $I_F = 40\text{ A}, V_R = 600\text{ V}$ $di_F/dt = 500\text{ A}/\mu\text{s}$	t_{rr}	–	86	–	ns
Reverse recovery charge		Q_{rr}	–	0.56	–	μC
Reverse recovery current		I_{rrm}	–	12	–	A
Diode peak rate of fall of reverse recovery current during t_b		di_{rrm}/dt	–	–210	–	$\text{A}/\mu\text{s}$

NGTB40N120L3WG

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
DIODE CHARACTERISTICS						
Reverse recovery time	$T_J = 125^\circ\text{C}$ $I_F = 40\text{ A}$, $V_R = 600\text{ V}$ $di_F/dt = 500\text{ A}/\mu\text{s}$	t_{rr}	–	136	–	ns
Reverse recovery charge		Q_{rr}	–	1.47	–	μC
Reverse recovery current		I_{rrm}	–	20	–	A
Diode peak rate of fall of reverse recovery current during t_b		dI_{rrm}/dt	–	–212	–	$\text{A}/\mu\text{s}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NGTB40N120L3WG

TYPICAL CHARACTERISTICS

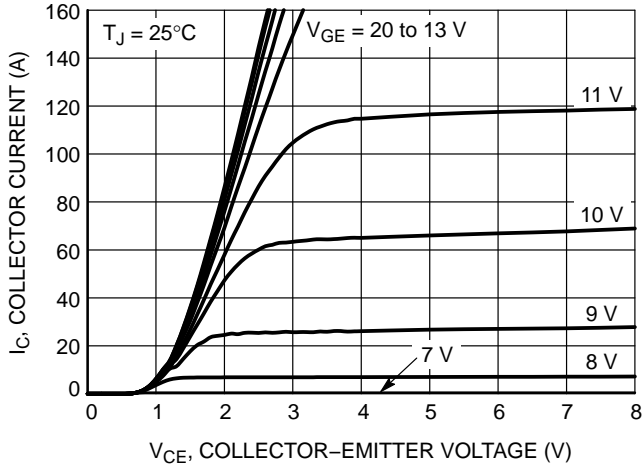


Figure 1. Output Characteristics

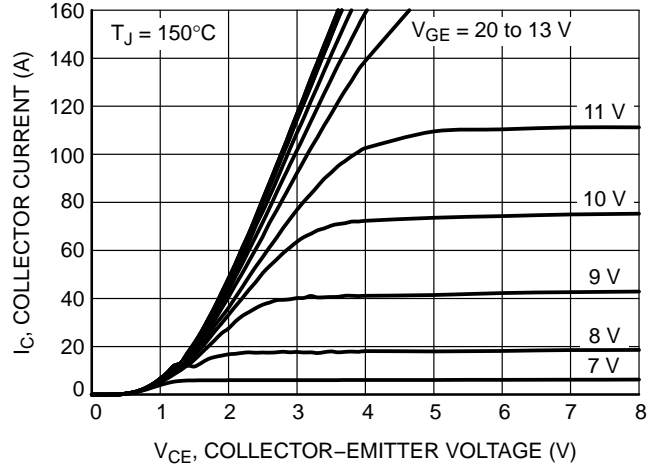


Figure 2. Output Characteristics

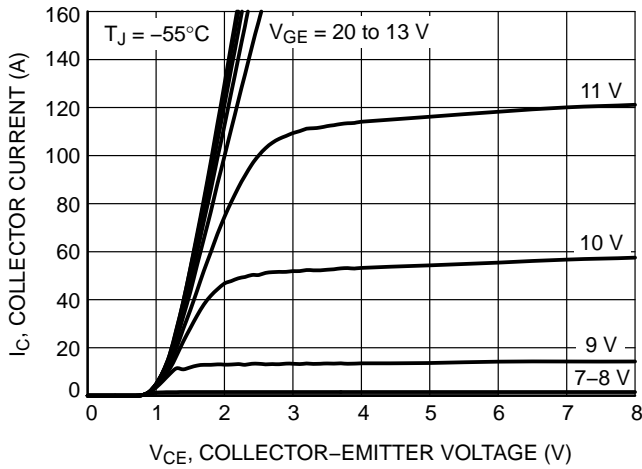


Figure 3. Output Characteristics

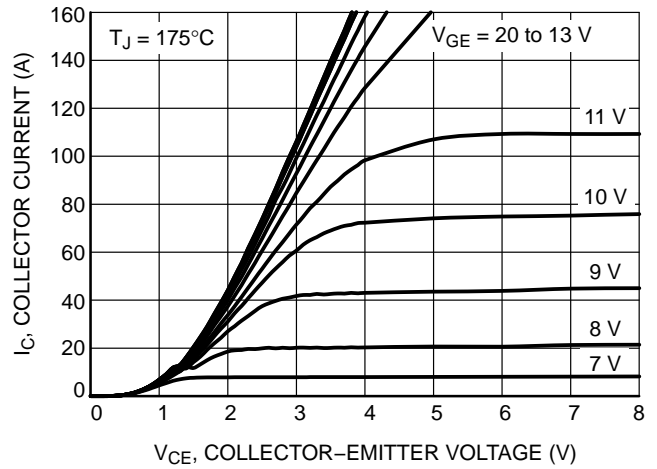


Figure 4. Output Characteristics

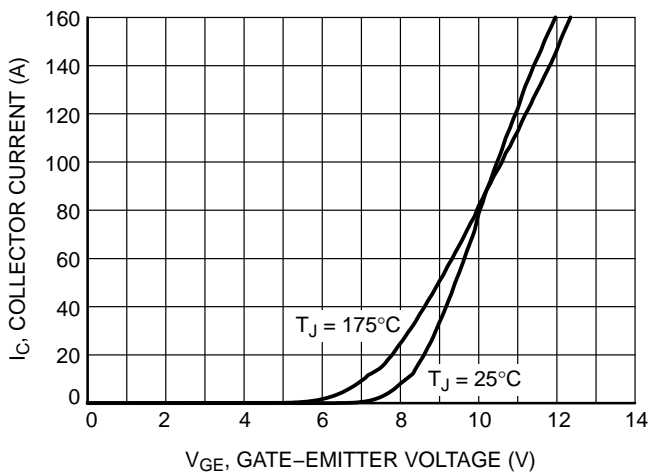


Figure 5. Typical Transfer Characteristics

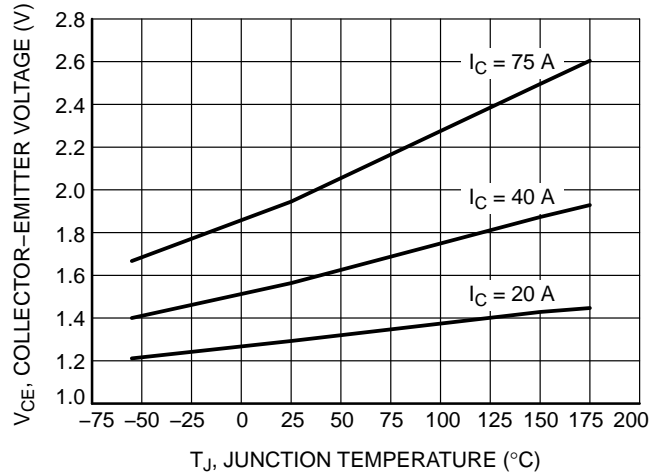


Figure 6. $V_{CE(sat)}$ vs. T_J

NGTB40N120L3WG

TYPICAL CHARACTERISTICS

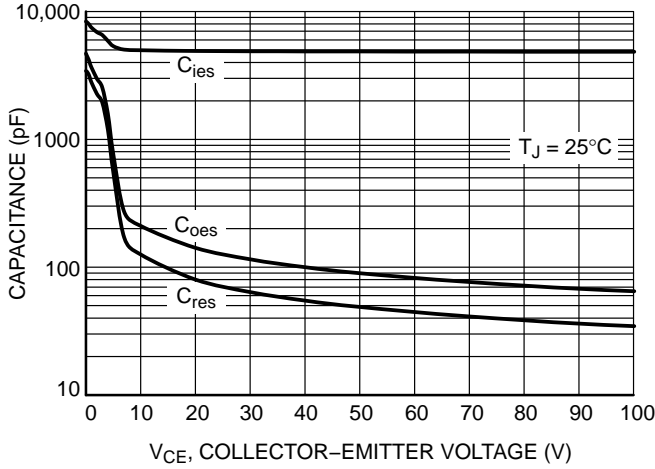


Figure 7. Typical Capacitance

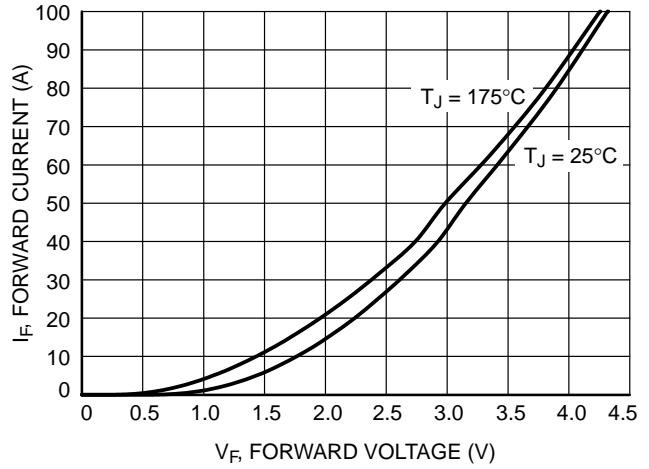


Figure 8. Diode Forward Characteristics

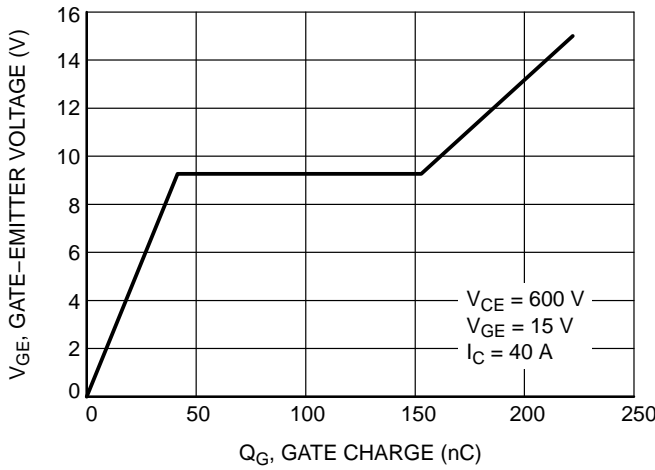


Figure 9. Typical Gate Charge

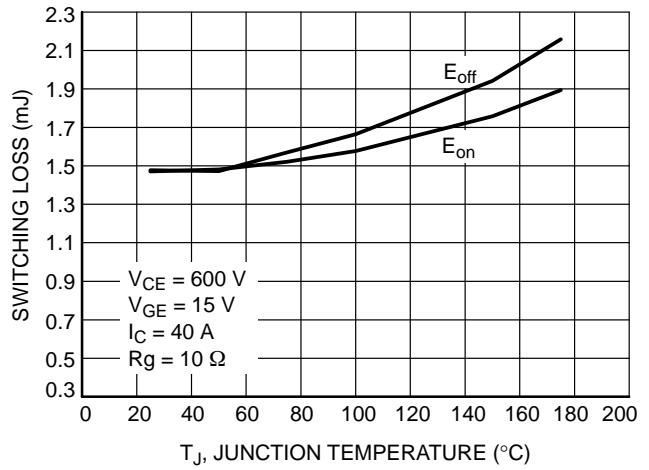


Figure 10. Switching Loss vs. Temperature

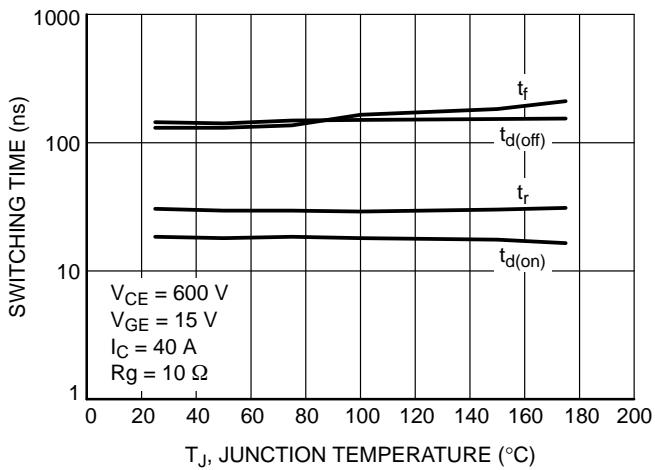


Figure 11. Switching Loss vs. Temperature

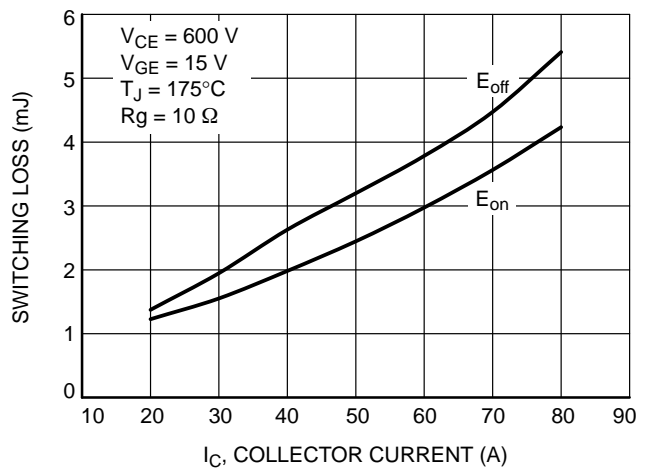


Figure 12. Switching Loss vs. I_C

NGTB40N120L3WG

TYPICAL CHARACTERISTICS

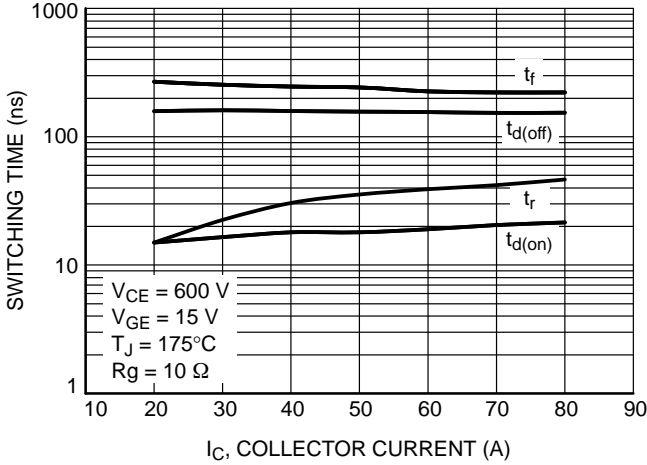


Figure 13. Switching Time vs. I_C

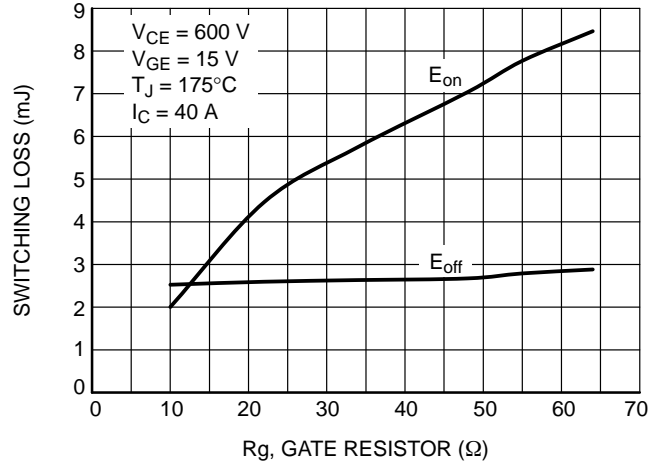


Figure 14. Switching Loss vs. R_g

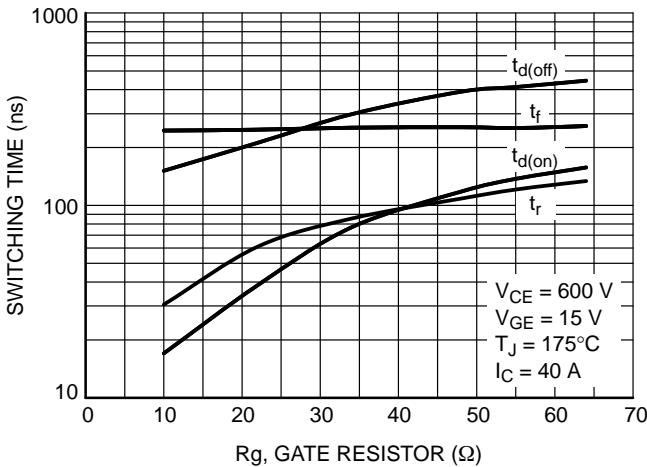


Figure 15. Switching Time vs. R_g

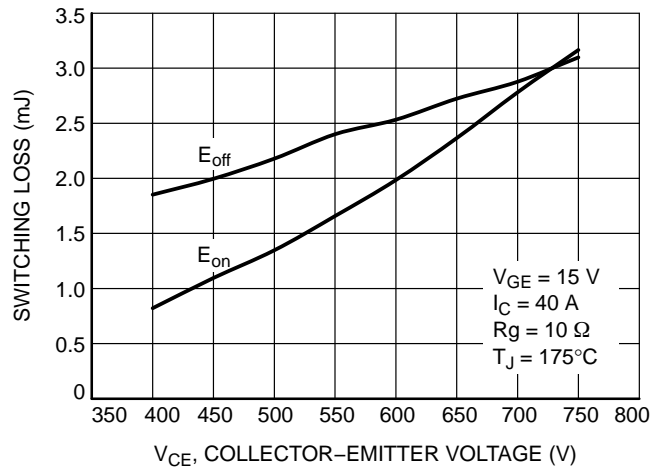


Figure 16. Switching Loss vs. V_{CE}

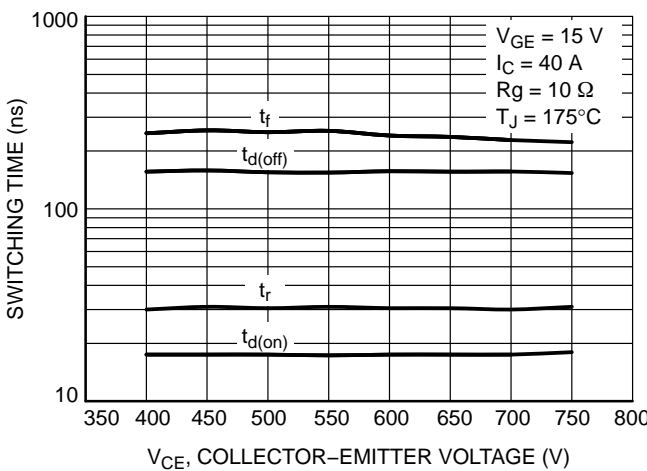


Figure 17. Switching Time vs. V_{CE}

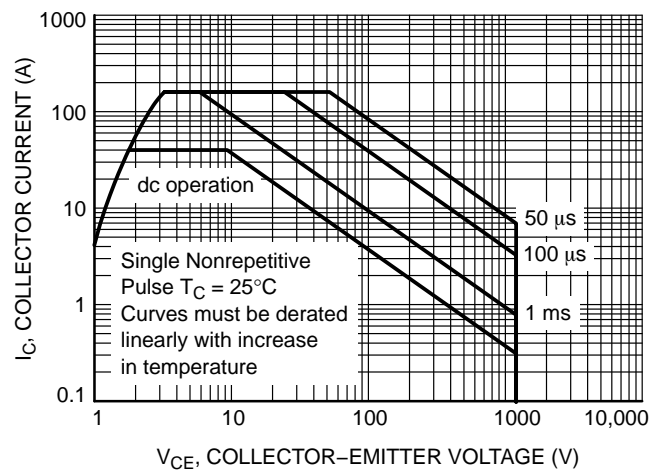


Figure 18. Safe Operating Area

NGTB40N120L3WG

TYPICAL CHARACTERISTICS

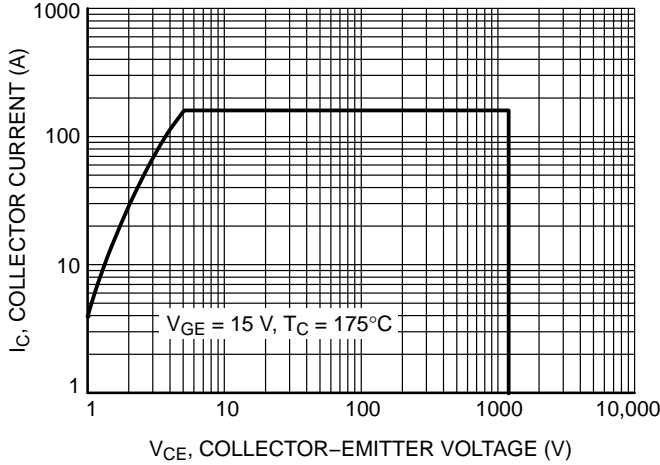


Figure 19. Reverse Bias Safe Operating Area

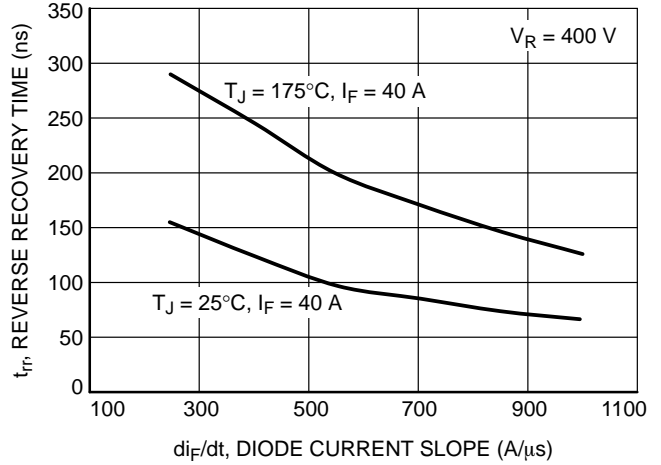


Figure 20. t_{rr} vs. di_F/dt

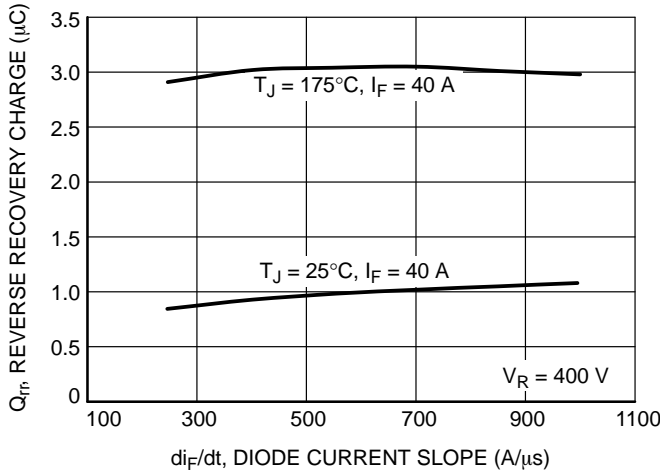


Figure 21. Q_{rr} vs. di_F/dt

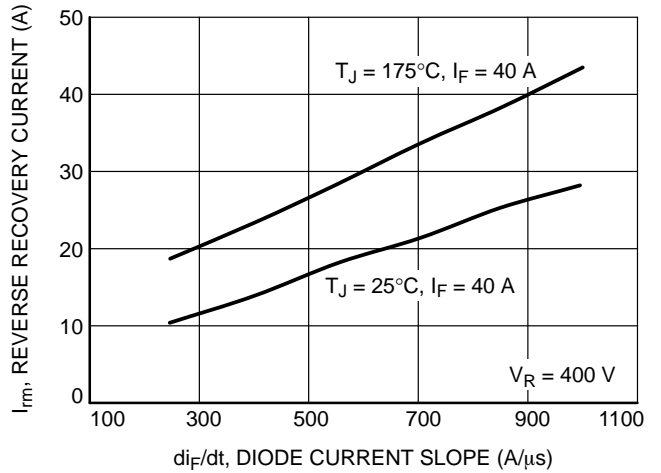


Figure 22. I_{rm} vs. di_F/dt

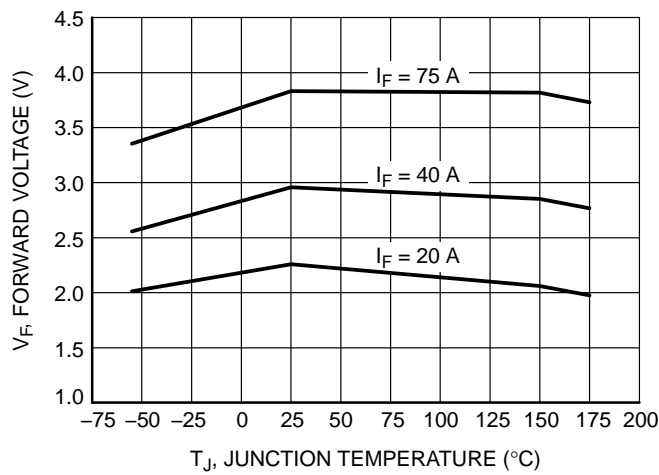


Figure 23. V_F vs. T_J

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TYPICAL CHARACTERISTICS

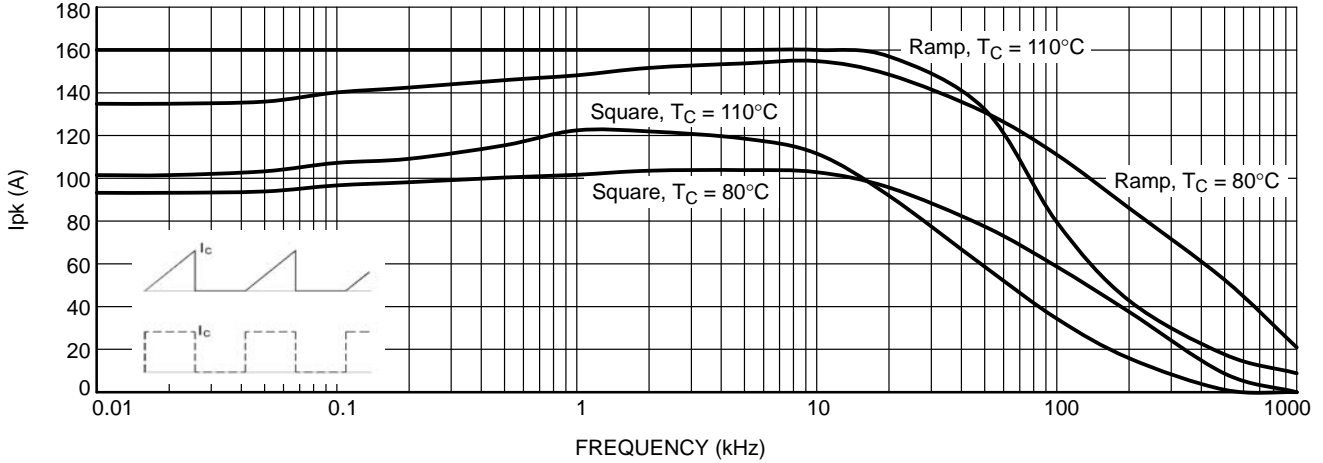


Figure 24. Collector Current vs. Switching Frequency

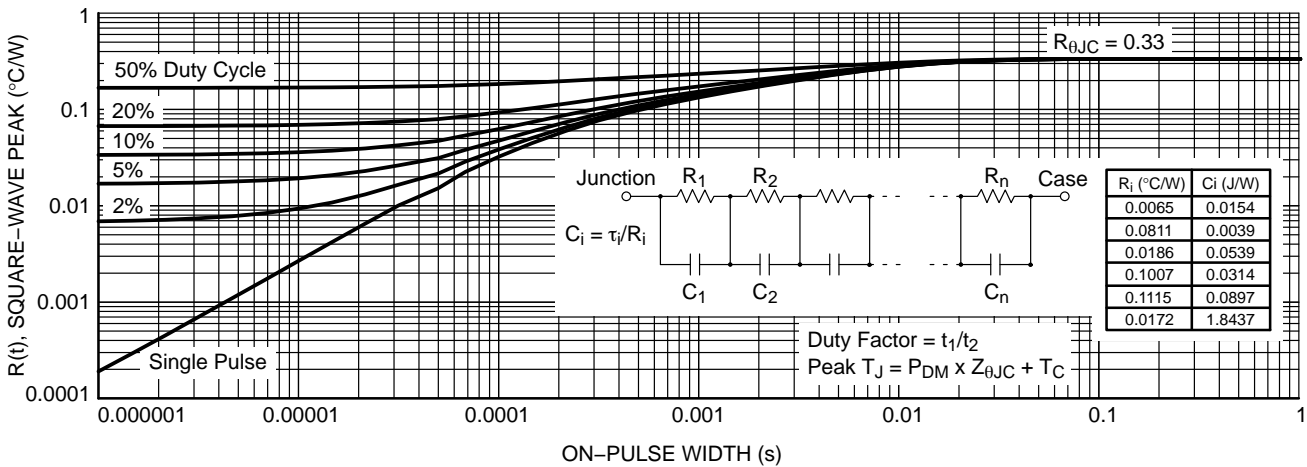


Figure 25. IGBT Transient Thermal Impedance

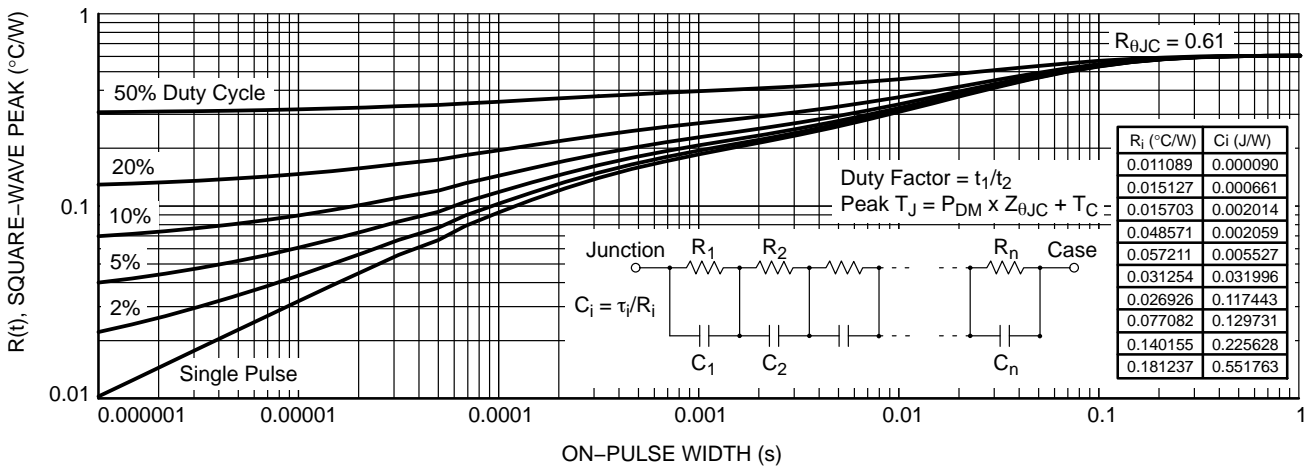


Figure 26. Diode Transient Thermal Impedance

NGTB40N120L3WG



Figure 27. Test Circuit for Switching Characteristics



Figure 28. Definition of Turn On Waveform

NGTB40N120L3WG

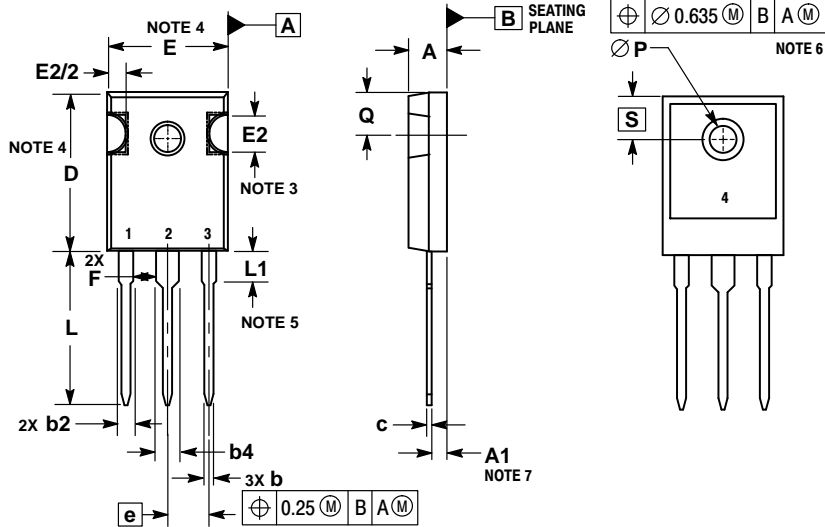


Figure 29. Definition of Turn Off Waveform

NGTB40N120L3WG

PACKAGE DIMENSIONS

TO-247 CASE 340AL ISSUE D



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
6. $\varnothing P$ SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS	
	MIN	MAX
A	4.70	5.30
A1	2.20	2.60
b	1.07	1.33
b2	1.65	2.35
b4	2.60	3.40
c	0.45	0.68
D	20.80	21.34
E	15.50	16.25
E2	4.32	5.49
e	5.45 BSC	
F	2.655	---
L	19.80	20.80
L1	3.81	4.32
P	3.55	3.65
Q	5.40	6.20
S	6.15 BSC	

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